

FORM PTO-147

**INFORMATION DISCLOSURE CITATION**Atty Docket  
0140/00268Serial No.  
To be assignedApplicant  
Arpan P. Mahorowala et al.Filing Date  
HerewithGroup Art Unit  
To be assigned**U.S. PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Name	Class	Sub-Class	Filing Date
CK	AA	5,985,524	11/16/99	Allen, et al.			3/28/97
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

**FOREIGN PATENT DOCUMENTS**

		Document Number	Date	Country	Class	Sub-Class	Translation
	AL						Yes No
	AM						Yes No
	AN						Yes No
	AO						Yes No
	AP						Yes No

**OTHER** (Including Author, Title, Date, Pertinent Pages, etc.)

CK	AR		A High Resolution 248 nm Bilayer Resist, Qinghuang Lin, et al., Part of the SPIE Conference on Advances in Resist Technology and Processing XVI; SPIE Vo. 3678; Santa Clara, CA (March 1999)
CK	AS		Lateral-only Photoresist Trimming for sub-80 nm Gate Stack Definition; Arpan P. Mahorowala; IBM (June, 2000)
CK	AT		Low Temperature Etching of Silylated Resist in an Oxygen Plasma Generated by an Electron Cyclotron Resonance Source; K.T. Sung; J. Electrochem. Soc., Vol. 140, No. 12 (December 1993)

Examiner *Christy Horacek*

Date Considered 3/21/03

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 600. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant(s).